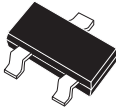


CMPT5179

NPN SILICON RF TRANSISTOR



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT5179 type is an NPN silicon RF transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for low noise, high frequency amplifier and high output oscillator applications.

Marking code is C7H.

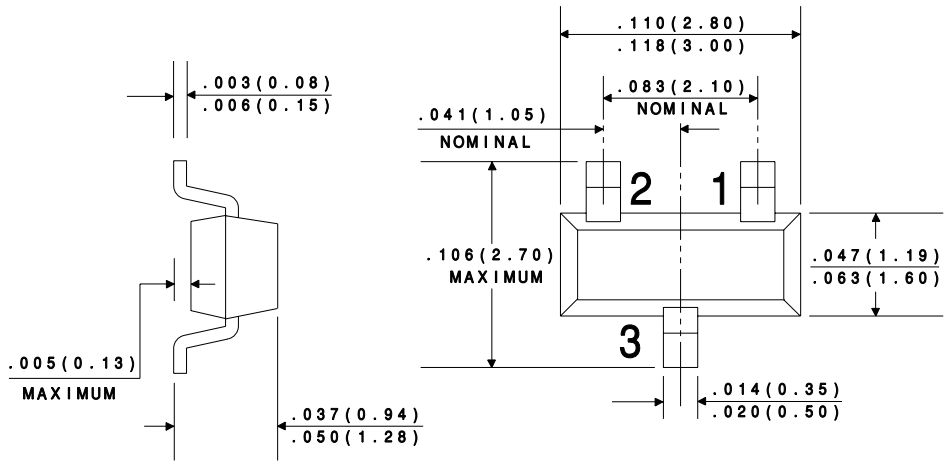
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	2.5	V
Collector Current	I_C	50	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	357	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=15\text{V}$			20	nA
BV_{CBO}	$I_C=10\mu\text{A}$	20			V
BV_{CEO}	$I_C=3.0\text{mA}$	12			V
BV_{EBO}	$I_E=10\mu\text{A}$	2.5			V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$			0.4	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$			1.0	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=3.0\text{mA}$	25			
f_T	$V_{CE}=6.0\text{V}, I_C=5.0\text{mA}, f=100\text{MHz}$	900	1450		MHz
C_{cb}	$V_{CB}=10\text{V}, I_E=0, f=0.1$ to 1.0MHz			1.0	pF
h_{fe}	$V_{CE}=6.0\text{V}, I_C=2.0, f=1.0\text{kHz}$	25			
G_{pe}	$V_{CE}=6.0\text{V}, I_C=5.0\text{mA}, f=200\text{MHz}$	15			dB
NF	$V_{CE}=6.0\text{V}, I_C=1.5\text{mA}, R_S=50\Omega, f=200\text{MHz}$			4.5	dB

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR